



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

**SURFACE MOUNT
SWITCHING DIODE**

VOLTAGE 80 Volts CURRENT 0.1 Ampere

CHN217UGP

APPLICATION

- * Ultra high speed switching

FEATURE

- * Small surface mounting type. (SC-70/SOT-323)
- * Two diode elements are connected in series (VFX2) per circuit.
- * Maximum total power dissipation is 200mW.
- * Peak forward current is 300mA.

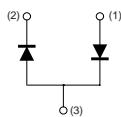
CONSTRUCTION

- * Silicon epitaxial planar

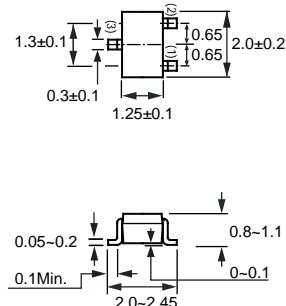
MARKING

- * A7

CIRCUIT



SC-70/SOT-323



Dimensions in millimeters

SC-70/SOT-323

MAXIMUM RATINGS (At TA = 25°C unless otherwise noted)

| RATINGS | SYMBOL | CHN217UGP | UNITS |
|--|------------------|-------------|-------|
| Maximum Recurrent Peak Reverse Voltage | V _{RRM} | 80 | Volts |
| Maximum RMS Voltage | V _{RMS} | 56 | Volts |
| Maximum DC Blocking Voltage | V _D | 80 | Volts |
| Maximum Average Forward Rectified Current | I _O | 0.1 | Amps |
| Peak Forward Surge Current at 1uSec. | I _{FSM} | 4.0 | Amps |
| Typical Junction Capacitance between Terminal (Note 1) | C _J | 2.0 | pF |
| Maximum Operating Temperature Range | T _J | +150 | °C |
| Storage Temperature Range | T _{STG} | -55 to +150 | °C |

ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

| CHARACTERISTICS | SYMBOL | CHN217UGP | UNITS |
|---|----------------|-----------|-------|
| Maximum Instantaneous Forward Voltage at I _F = 100mA | V _F | 1.20 | Volts |
| Maximum Average Reverse Current at V _R = 70V | I _R | 0.2 | uAmps |

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 6.0 volts.
2. ESD sensitive product handling required.

2002-5

RATING CHARACTERISTIC CURVES (CHN217UGP)

FIG. 1 - FORWARD CHARACTERISTICS

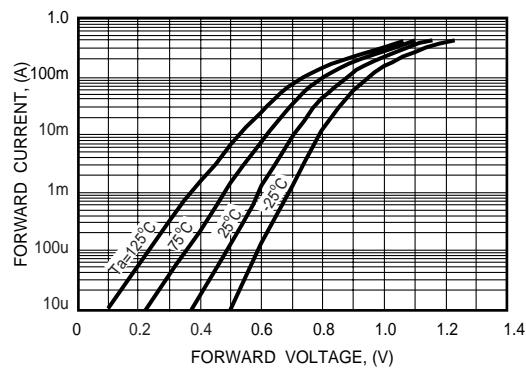


FIG. 2 - REVERSE CHARACTERISTICS

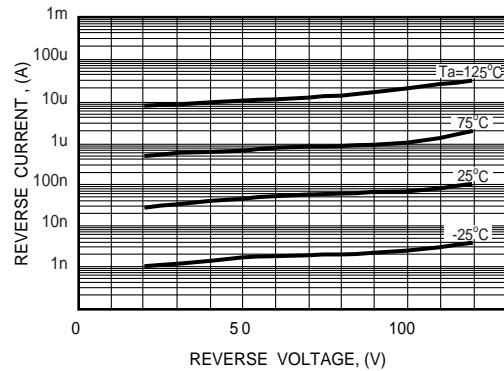


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

